

**AMENDMENTS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**In the Claims**

Claim 1(currently amended): A semiconductor light emitting devise comprising.

a substrate;

an n-type layer provided on the substrate and made of a nitride semiconductor material;

a multiple quantum well structure active layer including a plurality of well layers each made of  $\text{In}_x\text{Ga}_{(1-x-y)}\text{Al}_y\text{N}$  ( $0 \leq x, 0 \leq y, x+y < 1$ ) and a plurality of barrier layers each glade of  $\text{In}_2\text{Ga}_{(1-s-t)}\text{Al}_t\text{N}$  ( $0 \leq s, 0 \leq t, s+t < 1$ ), the multiple quantum well structure active layer being provided on then-type layer, and

A<sup>1</sup>  
a p-type layer provided on the multiple quantum well structure active layer and made of a nitride semiconductor material,

wherein the p-type layer contains hydrogen, and the hydrogen concentration of the p-type layer is greater than or equal to about  $1 \times 10^{16}$  atoms/cm<sup>3</sup> and less than or equal to about  $1 \times 10^{19}$  atoms/cm<sup>3</sup>, and

the p-type layer contains Mg and the Mg concentration of the p-type layer is greater than or equal to about  $4 \times 10^{19}$  atoms/cm<sup>3</sup> and less than or equal to about  $1 \times 10^{21}$  atoms/cm<sup>3</sup>.

Claim 2 (cancelled)

Claim 3 (original): A semiconductor light emitting device according to claim 1, further comprising a p-type electrode for applying a voltage via the p-type layer to the multiple quantum

well structure active layer, wherein the p-type electrode contains atoms selected from the group consisting of Pd, Sc, Y, La, Ce, Pr, Nd, Sm, Eu, Tb, Ti, Zr, Hf, V, Nb and Ta.

**Claim 4 (cancelled)**

**Claim 5 (original):** A semiconductor light emitting device according to claim 1, the hydrogen concentration of the n-type layer is less than or equal to  $1 \times 10^{17}$  atoms/cm<sup>3</sup>.

**Claim 6 (currently amended):** A semiconductor light emitting device according to ~~claim 4~~ claim 3, the hydrogen concentration of the n-type layer is less than or equal to  $1 \times 10^{17}$  atoms/cm<sup>3</sup>.

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A*  
**Claim 7 (original):** A semiconductor light emitting device according to claim 1, further comprising a layer including Al, wherein the p-type layer is provided, via the layer including Al, on the multiple quantum well structure active layer.

**Claim 8 (original):** A semiconductor light emitting device according to claim 7, the layer including Al has a thickness of about 5 nm or more.

**[Claims 9-10 (withdrawn)]**

**Claim 11 (new):** A semiconductor light emitting device comprising: a substrate; an n-type layer provided on the substrate and made of a nitride semiconductor material;

a multiple quantum well structure active layer including a plurality of well layers each made of  $In_xGa_{(1-x-y)}Al_yN$  ( $0 \leq x, 0 \leq y, x+y < 1$ ) and a plurality of barrier layers each made of  $In_2Ga_{(1-s-t)}Al_tN$  ( $0 \leq s, 0 \leq t, s+t < 1$ ), the multiple quantum well structure active layer being provided on the n-type layer; and

a p-type layer provided on the multiple quantum well structure active layer and made of a nitride semiconductor material,

wherein the p-type layer contains hydrogen, and the hydrogen concentration of the p-type layer is greater than or equal to about  $1 \times 10^{16}$  atoms/cm<sup>3</sup> and less than or equal to about  $1 \times 10^{19}$  atoms/cm<sup>3</sup>, and

the n-type layer contains hydrogen, and the hydrogen concentration of the n-type layer is less than or equal to  $1 \times 10^{17}$  atoms/cm<sup>3</sup>.

*Claim 12 (new): A semiconductor light emitting device according to claim 11, further comprising a p-type electrode for applying a voltage via the p-type layer to the multiple quantum well structure active layer, wherein the p-type electrode contains atoms selected from the group consisting of Pd, Sc, Y, La, Ce, Pr, Nd, Sm, Bu, Tb, Ti, Zr, Hf, V, Nb and Ta.*

*Claim 13 (new): A semiconductor light emitting device according to claim 11, further comprising a layer including Al, wherein the p-type layer is provided, via the layer including Al, on the multiple quantum well structure active layer.*

*Claim 14 (new): A semiconductor light emitting device according to claim 13, the layer including Al has a thickness of about 5 nm or more.*

*Claim 15 (new): A semiconductor light emitting device according to claim 11, wherein the p-type layer contains Mg, and the Mg concentration of the p-type layer is greater than or equal to about  $4 \times 10^{19}$  atoms/cm<sup>3</sup> and less than or equal to about  $1 \times 10^{21}$  atoms/cm<sup>3</sup>.*

*Claim 16 (new): A semiconductor light emitting device comprising: a substrate; an n-type layer provided on the substrate and made of a nitride semiconductor material;*

a multiple quantum well structure active layer including a plurality of well layers each made of  $\text{In}_x\text{Ga}_{(1-x-y)}\text{Al}_y\text{N}$  ( $0 \leq x, 0 \leq y, x+y < 1$ ) and a plurality of barrier layers each made of  $\text{In}_2\text{Ga}_{(1-s-t)}\text{Al}_t\text{N}$  ( $0 \leq s, 0 \leq t, s+t < 1$ ), the multiple quantum well structure active layer being provided on the n-type layer, and

a p-type layer provided on the multiple quantum well structure active layer and made of a nitride semiconductor material,

wherein the p-type layer contains hydrogen, and the hydrogen concentration of the p-type layer is greater than or equal to about  $1 \times 10^{16}$  atoms/cm<sup>3</sup> and less than or equal to about  $1 \times 10^{19}$  atoms/cm<sup>3</sup>, and

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further comprising a p-type electrode for applying a voltage via the p-type layer to the multiple quantum well structure active layer, wherein the p-type electrode contains a combination of Au and Pd.

Claim 17 (new): A semiconductor light emitting device according to claim 16, wherein the p-type layer contains Mg, and the Mg concentration of the p-type layer is greater than or equal to about  $4 \times 10^{19}$  atoms/cm<sup>3</sup> and less than or equal to about  $1 \times 10^{21}$  atoms/cm<sup>3</sup>.

Claim 18 (new): A semiconductor light emitting device according to claim 16, wherein the n-type layer contains hydrogen and the hydrogen concentration of the n-type layer is less than or equal to  $1 \times 10^{17}$  atoms/cm<sup>3</sup>.